

Honghwi Park

List of Publications by Year in descending order

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15
papers

105
citations

1478505

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h-index

1372567

10
g-index

15
all docs

15
docs citations

15
times ranked

143
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|-----------|
| 1 | Simultaneous Extraction of the Grain Size, Single-Crystalline Grain Sheet Resistance, and Grain Boundary Resistivity of Polycrystalline Monolayer Graphene. <i>Nanomaterials</i> , 2022, 12, 206. | 4.1 | 2 |
| 2 | Layer-resolved release of epitaxial layers in III-V heterostructure via a buffer-free mechanical separation technique. <i>Science Advances</i> , 2022, 8, eabl6406. | 10.3 | 7 |
| 3 | Effects of Thermally Induced Phase Transition on the Negative Thermo-Optic Properties of Atomic-Layer-Deposited TiO ₂ Films. <i>ACS Applied Electronic Materials</i> , 2022, 4, 651-662. | 4.3 | 4 |
| 4 | Factors Determining the Resistive Switching Behavior of Transparent InGaZnO-Based Memristors. <i>Physica Status Solidi - Rapid Research Letters</i> , 2022, 16, . | 2.4 | 10 |
| 5 | Influence of Amorphous-to-Crystalline Transformation on the Negative Thermo-Optic Properties of TiO ₂ Films. <i>ECS Transactions</i> , 2021, 102, 151-158. | 0.5 | 0 |
| 6 | Influence of Amorphous-to-Crystalline Transformation on the Negative Thermo-Optic Properties of TiO ₂ Films. <i>ECS Meeting Abstracts</i> , 2021, MA2021-01, 1019-1019. | 0.0 | 0 |
| 7 | Evaluation of the average grain size of polycrystalline graphene using an electrical characterization method. <i>Solid-State Electronics</i> , 2021, 186, 108172. | 1.4 | 1 |
| 8 | High-Performance Oxide-Based p-n Heterojunctions Integrating p-SnO _x and n-InGaZnO. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 55676-55686. | 8.0 | 4 |
| 9 | Analytic model of spalling technique for thickness-controlled separation of single-crystalline semiconductor layers. <i>Solid-State Electronics</i> , 2020, 163, 107660. | 1.4 | 8 |
| 10 | Investigation of electrical characteristics of flexible CMOS devices fabricated with thickness-controlled spalling process. <i>Solid-State Electronics</i> , 2020, 173, 107901. | 1.4 | 5 |
| 11 | Effect of Graphene Doping Level near the Metal Contact Region on Electrical and Photoresponse Characteristics of Graphene Photodetector. <i>Sensors</i> , 2020, 20, 4661. | 3.8 | 3 |
| 12 | Extraction of intrinsic field-effect mobility of graphene considering effects of gate-bias-induced contact modulation. <i>Journal of Applied Physics</i> , 2020, 127, . | 2.5 | 5 |
| 13 | Effect of copper surface morphology on grain size uniformity of graphene grown by chemical vapor deposition. <i>Current Applied Physics</i> , 2019, 19, 1414-1420. | 2.4 | 7 |
| 14 | Multifunctional graphene sensor for detection of environment signals using a decoupling technique. <i>Solid-State Electronics</i> , 2019, 151, 40-46. | 1.4 | 8 |
| 15 | Optimized poly(methyl methacrylate)-mediated graphene-transfer process for fabrication of high-quality graphene layer. <i>Nanotechnology</i> , 2018, 29, 415303. | 2.6 | 41 |